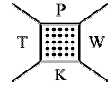




4ICSSC – 7PCCG

May 16÷20, 2004, Kościelisko, Zakopane, POLAND



PROGRAMME

Sunday, May 16

Reception from 16⁰⁰

18⁰⁰ – 20⁰⁰ Dinner

21⁰⁰ Welcome Reception

Monday, May 17

7⁰⁰ ÷ 8³⁰ Breakfast

8⁴⁵ **Opening Ceremony – Chair: Anna Pajączkowska**

9⁰⁰ ÷ 9⁴⁵ **Czochralski Lecture – Robert F. Sekerka**
*Equilibrium and Growth Shapes of Crystals:
How do they differ and why should we care?*

9⁴⁵ ÷ 10¹⁵ *Coffee Break*

Chair: Bogusław Mróz

10¹⁵ ÷ 10⁴⁵ **L (1)**
Luca Faraone
*Determination of carrier transport parameters in multi-layer
semiconductor Structures using mobility spectrum techniques*

10⁴⁵ ÷ 11¹⁵ **L (2)**
Izabella Grzegory
*GaN crystals grown under pressure - mechanisms of crystallization, physical
properties and applications*

11¹⁵ ÷ 11³⁰ **O (1)**
V. Kažukauskas, V. Kalendra, J.-V. Vaitkus
CARRIER TRANSPORT IN GaN SINGLE CRYSTALS AND RADIATION
DETECTORS INVESTIGATED BY THERMALLY STIMULATED SPECTROSCOPY

11³⁰ ÷ 12⁰⁰ *Coffee Break*

Chair: Detlef Klimm

12⁰⁰ ÷ 12³⁰ **L (3)**
Janusz Karpiński
*High pressure crystal growth and superconducting properties of pure and substituted
MgB₂*

12³⁰ ÷ 12⁴⁵ **O (2)**
R. Czernetzki, M. Leszczynski, I. Grzegory, P. Perlin, P. Prystawko, C. Skierbiszewski, M. Krysko, M. Sarzynski, P. Wisniewski, G. Nowak, A. Libura, S. Grzanka, T. Suski, L. Dmowski, E. Litwin-Staszewska, M. Bockowski, S. Porowski
MOVPE GROWTH OF NITRIDES SEMICONDUCTORS ON BULK GaN
CRYSTALS FOR BLUE-LASER TECHNOLOGY

13⁰⁰ ÷ 14⁰⁰ *Lunch*

Monday, May 17

Chair: Lorenzo Faraone

15⁰⁰ ÷ 15³⁰

L (4)

Maciej Bugajski

Design, fabrication and properties of high power semiconductor lasers

15³⁰ ÷ 15⁴⁵

O (3)

S. Macegoniuk, R. P. Sarzała, and **W. Nakwaski**

THE COMPREHENSIVE MODEL OF InP-BASED DIODE VERTICAL-CAVITY SURFACE-EMITTING LASERS

15⁴⁵ ÷ 16⁰⁰

O (4)

M. Dems and W. Nakwaski

A SIMPLIFIED ANALYTICAL APPROACH TO STRESS PROBLEMS IN MULTI-LAYERED NITRIDE DEVICES

16⁰⁰ ÷ 16³⁰

Coffee Break

chair: Akira Yoshikava

16³⁰ ÷ 17⁰⁰

L (5)

Koichi Kakimoto

Silicon crystal growth from the melt - analysis from atomic and macro scales

17⁰⁰ ÷ 17³⁰

L (6)

Isao Tanaka

Crystal growth of oxides by FZ method in magnetic field

17³⁰ ÷ 17⁴⁵

O (5)

A. Misiuk, A. Barcz, B. Surma, A. Wnuk and J. Jagielski

THE MICROSTRUCTURE OF CZOCHRALSKI SILICON CO-IMPLANTED WITH HELIUM AND HYDROGEN AND TREATED AT HIGH TEMPERATURE-PRESSURE

18⁰⁰ ÷ 19⁰⁰

Dinner

19⁰⁰ ÷ 21⁰⁰

Poster session **A**

20³⁰

PTWK General Meeting

Tuesday, May 18

7⁰⁰÷8¹⁵ Breakfast

8³⁰ ÷ 14⁰⁰ *Excursion*

14⁰⁰ ÷ 15⁰⁰ *Lunch*

Chair: Maria Suszyńska

16⁰⁰ ÷ 16³⁰ **L (7)**

Kimmo Saarinen

Compensating vacancy defects in n-type and p-type GaN

16³⁰ ÷ 17⁰⁰ *Coffee Break*

Chair: Maria Lefeld- Sosnowska

17⁰⁰ ÷ 17³⁰ **L (8)**

Wolfgang Neumann

Structural and chemical characterization of modern nanostructured materials

17³⁰ ÷ 18⁰⁰ **L (9)**

Zuzanna Liliental

Defects in GaN grown on Al₂O₃; Influence of p-doping

18⁰⁰ ÷ 19⁰⁰ *Dinner*

19⁰⁰ ÷ 21⁰⁰ **Poster Session B**

20³⁰ Meeting of PSCG Council and Sections)

Wednesday, May 19

7⁰⁰ ÷ 8¹⁵ Breakfast

Chair: Włodzimierz Nakwaski

8³⁰ ÷ 9⁰⁰

L (10)

Stephan Figge and Detlef Hommel

Future trends in short wavelength laser diodes

9⁰⁰ ÷ 9³⁰

L (11)

Masami Tatsumi

Single crystal growth and characterization of compound semiconducting material

9³⁰ ÷ 9⁴⁵

O (6)

D. Klimm, R. Uecker and P. Reiche

MELTING BEHAVIOUR AND GROWTH OF COLQUIRIITE LASER CRYSTALS

9⁴⁵ ÷ 10⁰⁰

O (7)

K. Conder, E. Pomjakushina

SINGLE CRYSTALS OF Na_xCoO₂ PREPARED BY TRAVELING SOLVENT FLOATING ZONE METHOD

10⁰⁰ ÷ 10³⁰

Coffee Break

Chair: Keshra Sangwal

10³⁰ ÷ 11⁰⁰

L (12)

Akira Yoshikawa

Growth and luminescent feature of novel oxide single crystal scintillators

11⁰⁰ ÷ 11³⁰

L (13)

Marek Godlewski

In-depth and in-plane profiling of light emission properties from semiconductor-based heterostructures

11³⁰ ÷ 11⁴⁵

O (8)

S. Ganschow and D. Klimm

GROWTH OF FORSTERITE - RICH OLIVINE SINGLE CRYSTALS

12⁴⁵ ÷ 12⁰⁰

O (9)

Reza Faiez

INSTABILITY AND BUBBLE ENTRAPMENT MECHANISMS IN CZ-CRYSTAL GROWTH

12¹⁵ ÷ 12³⁰

O (10)

A.E.Kokh, V.N.Popov, T.B.Bekker, N.G.Kononova, B.G.Nenashev, P.V.Mokrushnikov, K.A.Kokh, V.A.Vlezko

HEAD FIELD ROTATION METHOD AS A NEW APPROACH FOR THE HEAT-MASS-TRANSFER PROCESSES CONTROL OVER BY DIFFERENT CRYSTAL GROWTH TECHNIQS

13⁰⁰ ÷ 14⁰⁰

Lunch

Wednesday, May 19

Chair: Marian Herman

15⁰⁰ ÷ 15³⁰ **L (14)**
Gottfried Strasser
Design, growth and processing of GaAs-based quantum cascade lasers

15³⁰ ÷ 16⁰⁰ **L (15)**
Grzegorz Gładyszewski
Specular and nonspecular X-ray diffraction profiles of multilayered structures

16⁰⁰ ÷ 16³⁰ *Coffee Break*

Chair: Antoni Rogalski

16³⁰ ÷ 17⁰⁰ **L (16)**
Andrzej Jeleński
New materials and metamaterials for electronics and optoelectronics

17⁰⁰ ÷ 17³⁰ **L (17)**
Mauro Tonelli
Fluoride crystals for visible and IR laser applications

17¹⁵ ÷ 17³⁰ **O (11)**
K. Kamada, T. Satonaga, A. Yoshikawa, H. Sato, M. Nikl, Y. Waseda,
T. Fukuda, H. Koike
CRYSTAL GROWTH AND SCINTILLATION PROPERTIES
OF Ce-DOPED PrF₃ SINGLE CRYSTALS

17³⁰ ÷ 17⁴⁵ **O (12)**
L.J. Liu and K. Kakimoto
3D GLOBAL ANALYSIS OF CZ-SI CRYSTAL GROWTH IN A TRANSVERSE
MAGNETIC FIELD WITH ROTATING CRUCIBLE AND CRYSTAL

17⁴⁵ ÷ 18⁰⁰ **O (13)**
G. Dhanaraj, M. Dudley, **F. Liu**, H. Zhang and V. Prasad
GROWTH AND STRUCTURAL DEFECTS CHARACTERIZATION
OF 6H SiC CRYSTALS

19⁰⁰ *Banquet – bonfire*
Doctoral dissertation-PTWK prize

Thursday, May 20

7⁰⁰ ÷ 8¹⁵ Breakfast

Chair: Bożena Hilczer

9⁰⁰ ÷ 9¹⁵

Lecture of doctoral dissertation winner

Magdalena Skutecka

ELECTRONIC STRUCTURE AND MAGNETIC PROPERTIES OF GdTAl (T-TRANSITION METAL) SINGLE CRYSTALS

9¹⁵ ÷ 9⁴⁵

L (18)

Kenji Nomura, Hideo Hosono

Reactive solid state epitaxy for thin film growth of transparent oxide semiconductors

9⁴⁵ ÷ 10¹⁵

L (19)

Sadik Dost,

Recent progress in electroepitaxial growth of compound semiconductors in magnetic field

10¹⁵ ÷ 10³⁰

O (14)

A. Piotrowski, W. Gawron, K. Kłos, P. Madejczyk, M. Romanis, M. Grudzień, A. Rogalski and J. Piotrowski

MOCVD GROWTH OF Hg_{1-x}Cd_xTe HETROSTRUCTURES FOR UNCOOLED INFRARED PHOTODETECTORS

10³⁰ ÷ 11⁰⁰

Coffee Break

Thursday, May 20

Chair: Stanisław Krukowski

11⁰⁰ ÷ 11³⁰

L (20)

Zbigniew Żytkiewicz

Growth and properties of epitaxial laterally overgrown semiconductor structures

11³⁰ ÷ 11⁴⁵

O (15)

J. T. Sadowski, T. Nagao, M. Saito, S. Yaginuma, G. E. Thayer, R. Tromp and T. Sakurai

THIN BISMUTH FILMS AS TEMPLATES FOR GROWTH OF HIGHLY ORDERED PENTACENE

11⁴⁵ ÷ 12⁰⁰

O (16)

J. Ciosek, W. Paszkowicz, J. Kubicki, P. Pankowski, T. Przesławski, W. Zaraska
MODIFICATION OF Cu-Al-O FILM MICROSTRUCTURE DURING POST-DEPOSITION ANNEALING

12⁰⁰ ÷ 12¹⁵

O (17)

S.M. Lee, T.I. Shin, H.J. Lee, and **D.H. Yoon**

HOLOGRAPHIC PROPERTIES OF MnO₂ : Tb₄O₇ CO DOPED NEAR STOICHIOMETRIC LiNbO₃ SINGLE CRYSTALS

12¹⁵ ÷ 12³⁰

O (18)

R.J. Iwanowski, M.H. Heinonen, E. Janik

CHARACTERIZATION OF Mn-Te BOND IN ZINC-BLENDE MnTe BY X-RAY SPECTROSCOPY

12³⁰

Closing – Chair: Stanisław Krukowski

13⁰⁰

Lunch